

isc Silicon NPN Power Transistor

2SC5197

DESCRIPTION

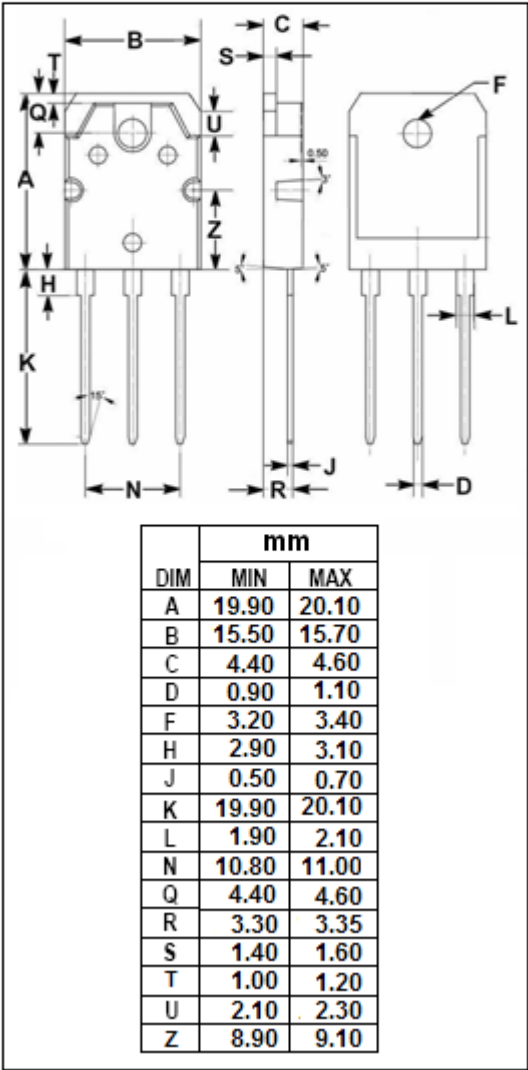
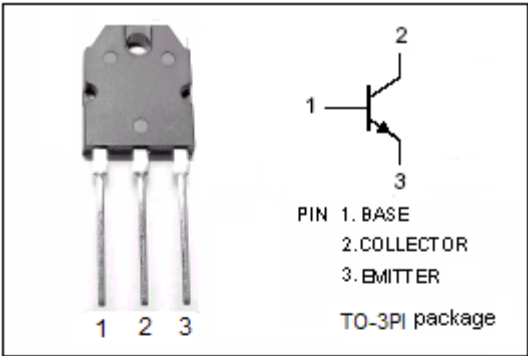
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Min}) @ I_C = 6A$
- Good Linearity of h_{FE}
- Complement to Type 2SA1940

APPLICATIONS

- Power amplifier applications
- Recommend for 55W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	0.8	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC5197****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $I_B=0$	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}$; $I_B=0.6\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=4\text{A}$; $V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=120\text{V}$; $I_E=0$			5	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}$; $I_C=0$			5	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$	55		160	
h_{FE-2}	DC Current Gain	$I_C=4\text{A}$; $V_{CE}=5\text{V}$	35			
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f_{test}=1.0\text{MHz}$		120		pF
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}$; $V_{CE}=5\text{V}$		30		MHz

◆ **h_{FE-1} Classifications**

R	O
55-110	80-160

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